

N-Channel Super Junction Power MOSFET IV

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

Features

- Optimized body diode reverse recovery performance
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)
- LLC Half-bridge

| | | |
|------------------------|-----|----|
| $V_{DS\ min@T_{jmax}}$ | 710 | V |
| $R_{DS(ON)TYP}$ | 680 | mΩ |
| I_D | 6 | A |
| Q_g | 7.2 | nC |



Schematic diagram

Package Marking And Ordering Information

| Device | Device Package | Marking |
|------------|----------------|------------|
| NCE65N760I | TO-251 | NCE65N760I |



TO-251

Table 1. Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|--|-----------------|------------|---------------------|
| Drain-Source Voltage ($V_{GS}=0V$) | V_{DS} | 650 | V |
| Gate-Source Voltage ($V_{DS}=0V$) AC ($f>1\text{ Hz}$) | V_{GS} | ± 30 | V |
| Gate-Source Voltage ($V_{DS}=0V$) DC | V_{GS} | ± 20 | V |
| Continuous Drain Current at $T_c=25^\circ\text{C}$ | $I_{D(DC)}$ | 6 | A |
| Continuous Drain Current at $T_c=100^\circ\text{C}$ | $I_{D(DC)}$ | 4.2 | A |
| Pulsed drain current (Note 1) | $I_{DM(pluse)}$ | 24 | A |
| Maximum Power Dissipation($T_c=25^\circ\text{C}$) | P_D | 73 | W |
| Derate above 25°C | | 0.49 | W/ $^\circ\text{C}$ |
| Avalanche current(Note 2) | I_{AS} | 2 | A |
| Drain Source voltage slope, $V_{DS} \leq 480\text{ V}$, | dv/dt | 50 | V/ns |
| Reverse diode dv/dt , $V_{DS} \leq 480\text{ V}, I_{SD} < I_D$ | dv/dt | 15 | V/ns |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55...+175 | $^\circ\text{C}$ |

* limited by maximum junction temperature

Table 2. Thermal Characteristic

| Parameter | Symbol | Value | Unit |
|---|------------|-------|-------------------------------|
| Thermal Resistance, Junction-to-Case (Maximum) | R_{thJC} | 2.05 | $^{\circ}\text{C} / \text{W}$ |
| Thermal Resistance, Junction-to-Ambient (Maximum) | R_{thJA} | 62 | $^{\circ}\text{C} / \text{W}$ |

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|--|--------------|---|-----|-----|-----------|---------------|
| On/off states | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 650 | | | V |
| Zero Gate Voltage Drain Current(Tc=25°C) | I_{DSS} | $V_{DS}=650V, V_{GS}=0V$ | | | 1 | μA |
| Zero Gate Voltage Drain Current(Tc=125°C) | I_{DSS} | $V_{DS}=650V, V_{GS}=0V$ | | | 100 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | | | ± 200 | nA |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 3 | 3.5 | 4 | V |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}=10V, I_D=3A$ | | 680 | 760 | m Ω |
| Dynamic Characteristics | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=50V, V_{GS}=0V,$ $F=1.0\text{MHz}$ | | 461 | | pF |
| Output Capacitance | C_{oss} | | | 14 | | pF |
| Reverse Transfer Capacitance | C_{rss} | | | 4 | | pF |
| Total Gate Charge | Q_g | $V_{DS}=480V, I_D=3A,$ $V_{GS}=10V$ | | 7.2 | | nC |
| Gate-Source Charge | Q_{gs} | | | 1.3 | | nC |
| Gate-Drain Charge | Q_{gd} | | | 1.3 | | nC |
| Gate plateau voltage | V_{gp} | | | 5.2 | | V |
| Intrinsic gate resistance | R_G | $f = 1 \text{ MHz open drain}$ | | 35 | | Ω |
| Switching times | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=480V, I_D=3A,$ $R_G=1.7\Omega, V_{GS}=10V$ | | 10 | | nS |
| Turn-on Rise Time | t_r | | | 7 | | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 55 | | nS |
| Turn-Off Fall Time | t_f | | | 8 | | nS |
| Source- Drain Diode Characteristics | | | | | | |
| Source-drain current(Body Diode) | I_{SD} | $T_C=25^{\circ}\text{C}$ | | | 6 | A |
| Pulsed Source-drain current(Body Diode) | I_{SDM} | | | | 24 | A |
| Forward On Voltage | V_{SD} | $T_j=25^{\circ}\text{C}, I_{SD}=6A, V_{GS}=0V$ | | 0.9 | 1.2 | V |
| Reverse Recovery Time | t_{rr} | $T_j=25^{\circ}\text{C}, I_F=3A,$ $di/dt=100A/\mu s$ | | 185 | | nS |
| Reverse Recovery Charge | Q_{rr} | | | 1.3 | | μC |
| Peak Reverse Recovery Current | I_{rrm} | | | 14 | | A |

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_j=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

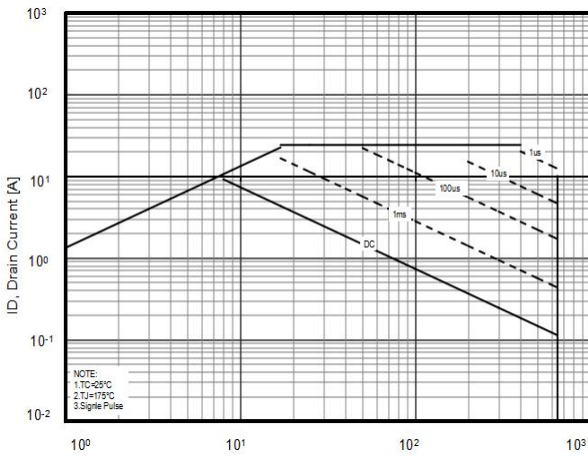


Figure2. Capacitance

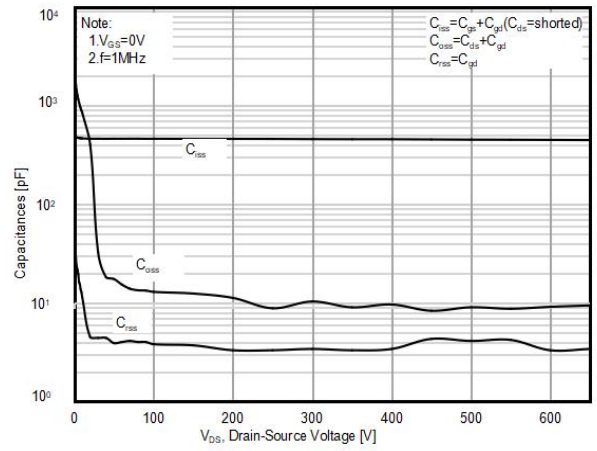


Figure3. Transfer characteristics

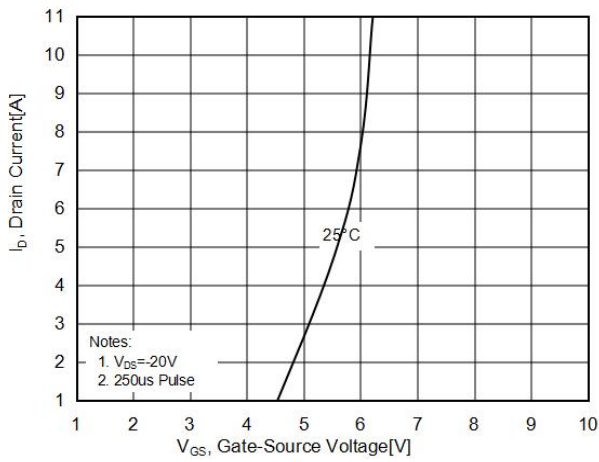


Figure4. Output characteristics

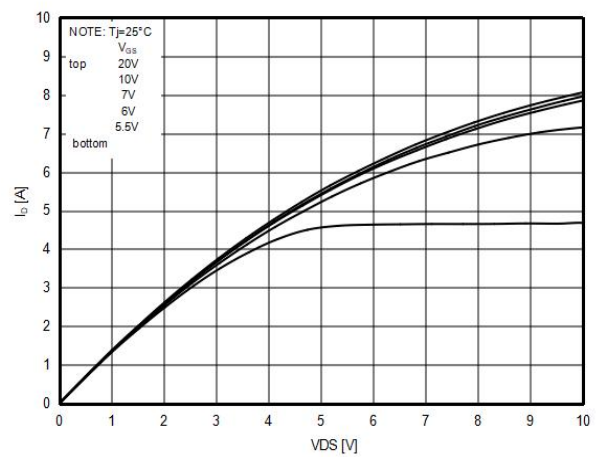


Figure5. $R_{DS(ON)}$ vs Junction Temperature

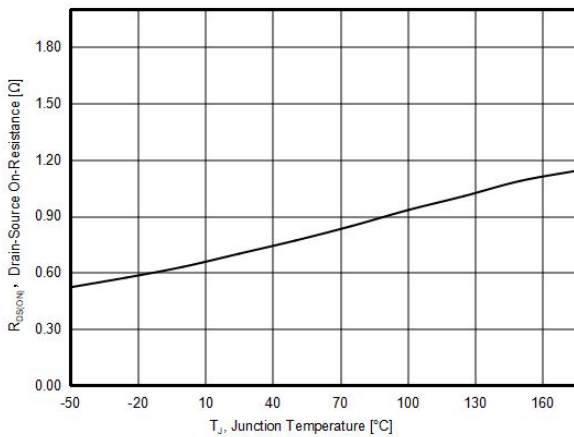


Figure6. BV_{DSS} vs Junction Temperature

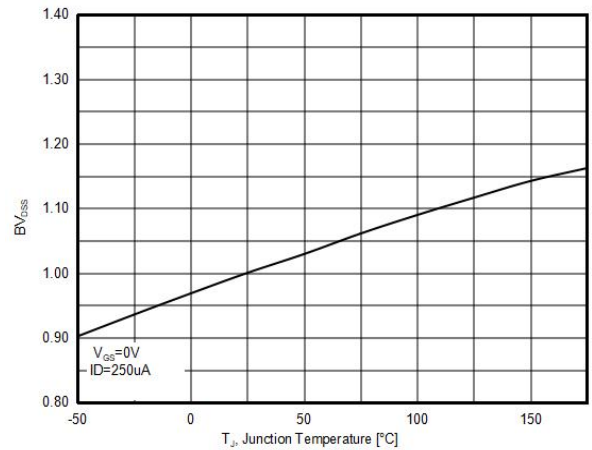


Figure7. Maximum I_D vs Junction Temperature

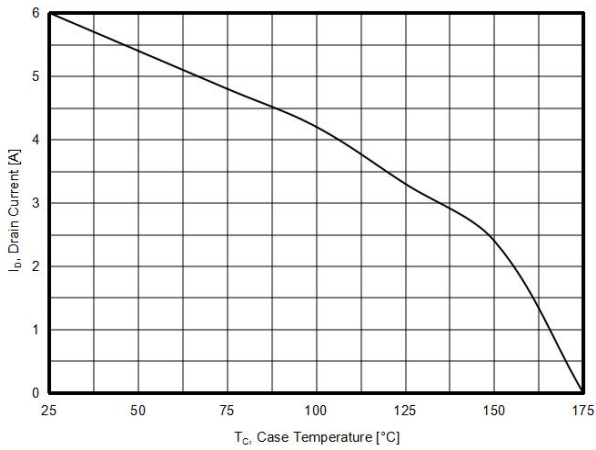


Figure8. Gate charge waveforms

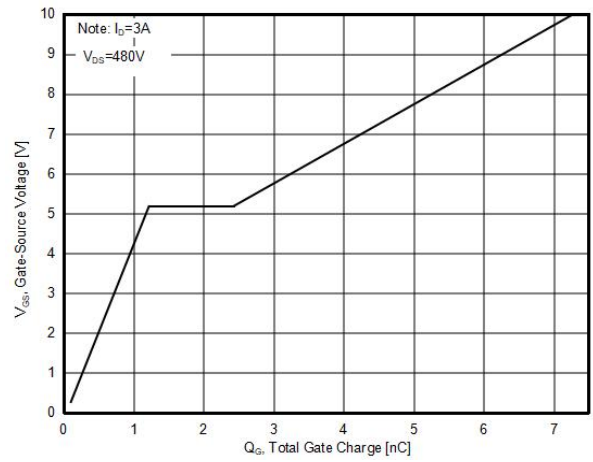


Figure9. Static drain-source on resistance

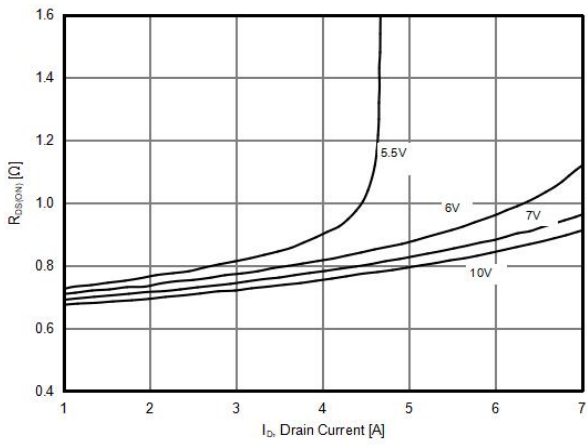
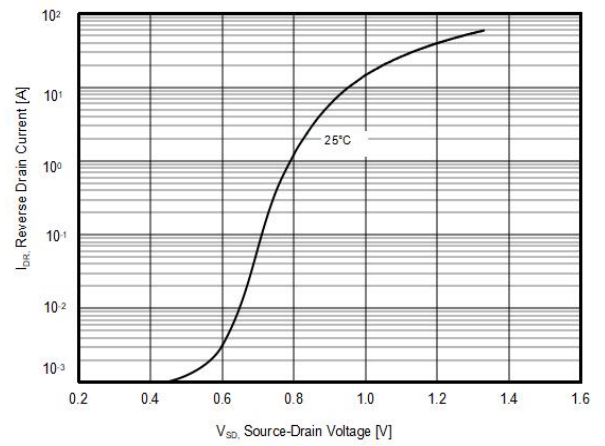
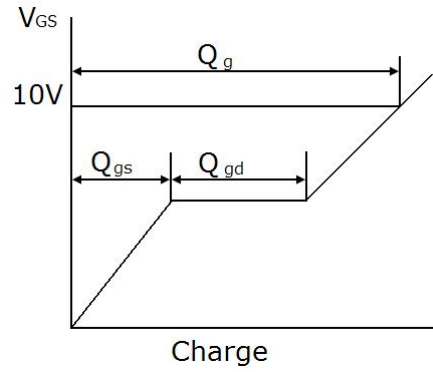
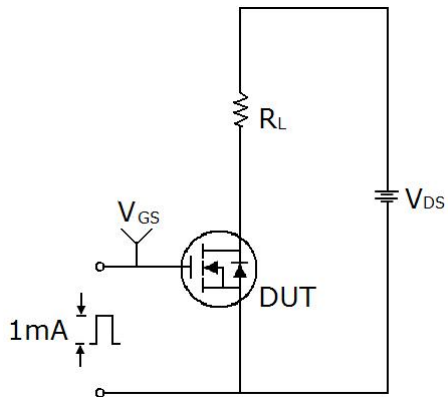


Figure10. Source-Drain Diode Forward Voltage

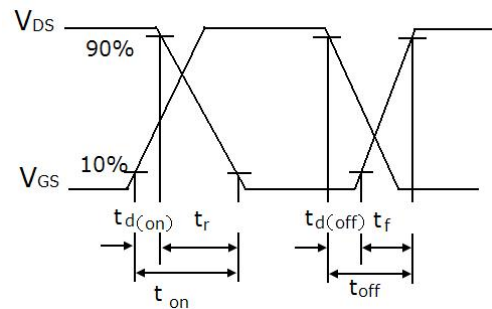
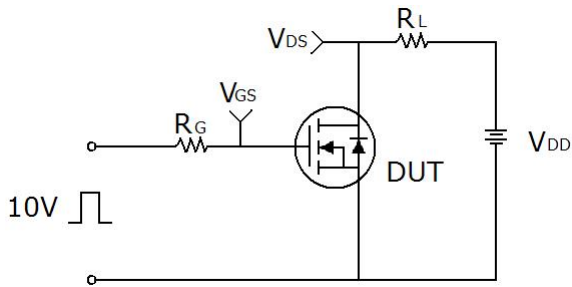


Test circuit

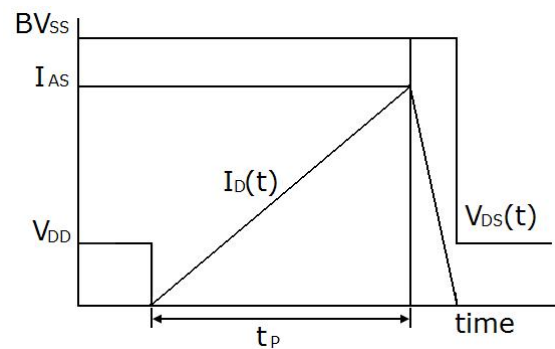
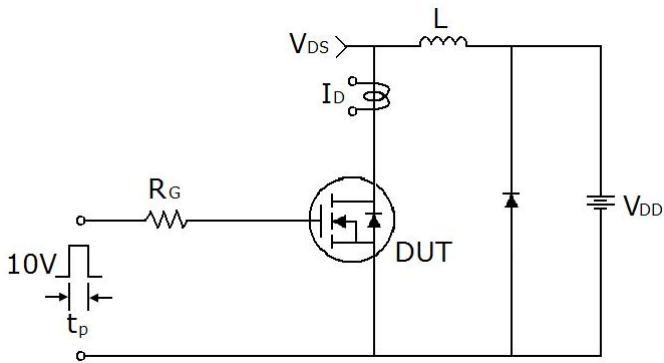
1) Gate charge test circuit & Waveform



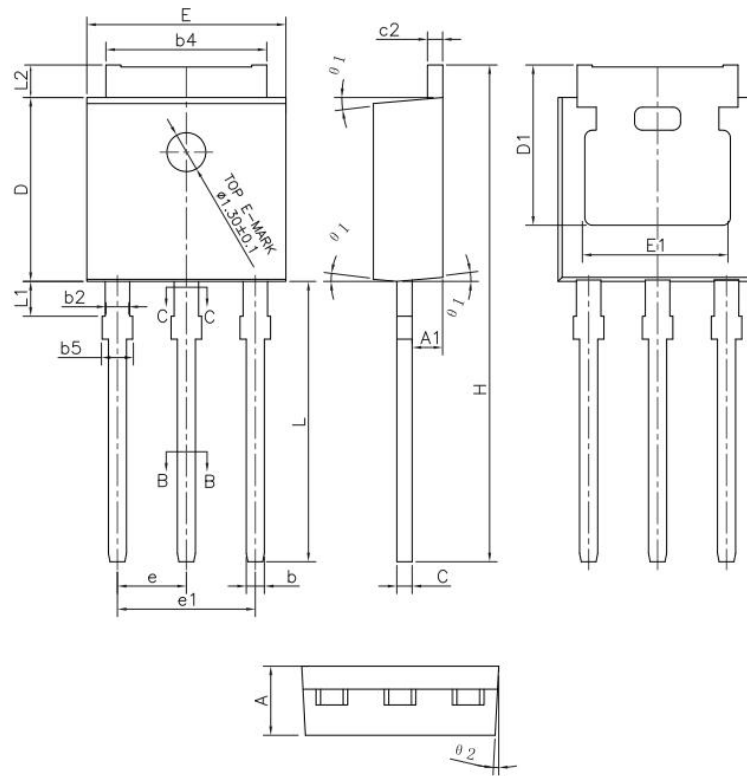
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms

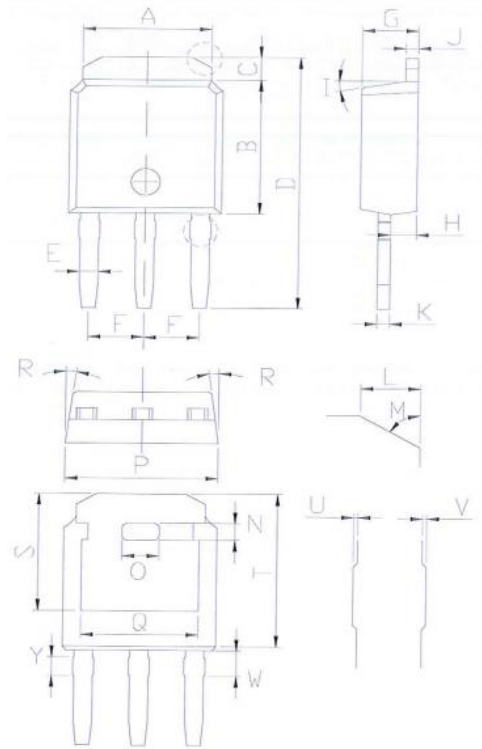


TO-251-P Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 2.20 | 2.35 | 0.087 | 0.093 |
| A1 | 0.90 | 1.10 | 0.035 | 0.043 |
| b | 0.56 | 0.69 | 0.022 | 0.027 |
| b1 | 0.55 | 0.65 | 0.022 | 0.026 |
| b2 | 0.77 | 0.90 | 0.030 | 0.035 |
| b3 | 0.76 | 0.86 | 0.030 | 0.034 |
| b4 | 5.23 | 5.43 | 0.206 | 0.214 |
| c | 0.46 | 0.59 | 0.018 | 0.023 |
| c1 | 0.45 | 0.55 | 0.018 | 0.022 |
| c2 | 0.46 | 0.59 | 0.018 | 0.023 |
| D | 6.00 | 6.20 | 0.236 | 0.244 |
| D1 | 5.20 | - | 0.205 | - |
| E | 6.50 | 6.70 | 0.256 | 0.264 |
| E1 | 4.60 | 5.00 | 0.181 | 0.197 |
| e | 2.24 | 2.34 | 0.088 | 0.092 |
| e1 | 4.47 | 4.67 | 0.176 | 0.184 |
| H | 16.18 | 16.78 | 0.637 | 0.661 |
| L | 9.00 | 9.60 | 0.354 | 0.378 |
| L1 | 0.95 | 1.35 | 0.037 | 0.053 |
| L2 | 0.90 | 1.25 | 0.035 | 0.049 |

TO-251-L Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 5.04 | 5.64 | 0.198 | 0.222 |
| B | 5.70 | 6.30 | 0.224 | 0.248 |
| C | 0.75 | 1.35 | 0.030 | 0.053 |
| D | 11.01 | 11.61 | 0.433 | 0.457 |
| E | 0.61 | 0.91 | 0.024 | 0.036 |
| F | 2.13 | 2.43 | 0.084 | 0.096 |
| G | 2.00 | 2.60 | 0.079 | 0.102 |
| H | 0.76 | 1.36 | 0.030 | 0.054 |
| J | 0.36 | 0.66 | 0.014 | 0.026 |
| K | 0.37 | 0.67 | 0.015 | 0.026 |
| L | 0.50 | 1.10 | 0.020 | 0.043 |
| N | 0.45 | 1.05 | 0.018 | 0.041 |
| O | 1.50 | 2.10 | 0.059 | 0.083 |
| P | 6.30 | 6.90 | 0.248 | 0.272 |
| Q | 4.55 | 5.15 | 0.179 | 0.203 |
| S | 5.00 | 5.60 | 0.197 | 0.220 |
| T | 6.60 | 7.20 | 0.260 | 0.283 |
| W | 0.90 | 1.40 | 0.035 | 0.055 |
| Y | 0.60 | 1.10 | 0.024 | 0.043 |

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